SLRS025A - DECEMBER 1976 - REVISED NOVEMBER 1995

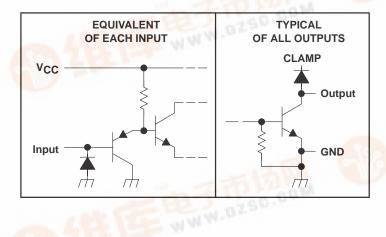
- Characterized for Use to 300 mA
- No Output Latch-Up at 55 V (After Conducting 300 mA)
- High-Voltage Outputs (100 V Typ)
- Output Clamp Diodes for Transient Suppression (300 mA, 70 V)
- TTL- or MOS-Compatible Diode-Clamped Inputs
- pnp Transistor Inputs Reduce Input Current
- Standard Supply Voltage
- Suitable for Hammer-Driver Applications
- Plastic DIP (P) With Copper-Lead Frame Provides Cooler Operation and Improved Reliability

### description

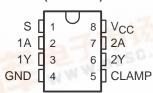
The SN75476 through SN75478 are dual peripheral drivers designed for use in systems that require high current, high voltage, and fast switching times. The SN75476, SN75477, and SN75478 provide AND, NAND, and OR drivers respectively. These devices have diode-clamped inputs as well as high-current, high-voltage clamp diodes on the outputs for inductive transient protection.

The SN75476, SN75477, and SN75478 drivers are characterized for operation from 0°C to 70°C.

### schematics of inputs and outputs



#### D OR P PACKAGE (TOP VIEW)



# Function Tables

SN75476 (each AND driver)

INPUTS		OUTPUT
A S		Υ
Н	Н	Н
L	X	L
X	L	L.C.

#### SN75477 (each NAND driver)

INPU	OUTPUT	
A S		Y
Н	Н	L
L	X	Н
X	L	Н

#### SN75478 (each OR driver)

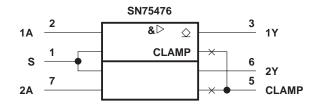
INPUTS		OUTPUT
Α	S	Υ
Н	Х	Н
X	Н	Н
L	L	L

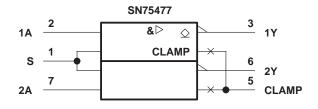
H = high level, L = low level X = irrelevant

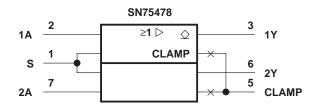
# SN75476 THRU SN75478 DUAL PERIPHERAL DRIVERS

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### logic symbols†

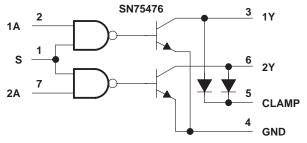




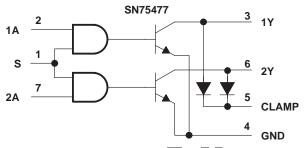


<sup>&</sup>lt;sup>†</sup> These symbols are in accordance with ANSI/IEEE Std 91-1984 and IEC publication 617-12.

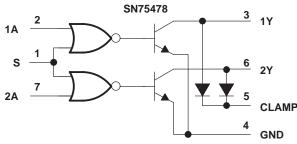
## logic diagrams (positive logic)



Positive Logic: Y = AS or  $\overline{A+S}$ 



Positive Logic:  $Y = \overline{AS}$  or  $\overline{A} + \overline{S}$ 



Positive Logic: Y = A + S or  $\overline{A} \, \overline{S}$ 



# SN75476 THRU SN75478 DUAL PERIPHERAL DRIVERS

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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V <sub>CC</sub> (see Note 1)	7 V
Input voltage, V <sub>I</sub>	5.5 V
Continuous output current (see Note 2)	400 mA
Peak output current: $t_w \le 10$ ms, duty cycle $\le 50\%$	500 mA
$t_W \le 30 \text{ ns}, \text{ duty cycle} \le 0.002\% \dots$	3 A
Output clamp current, IOK	400 mA
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T <sub>A</sub>	0°C to 70°C
Storage temperature range, T <sub>stg</sub>	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

NOTES: 1. Voltage values are with respect to network GND.

2. Both halves of this dual circuit may conduct rated current simultaneously; however, power dissipation averaged over a short time interval must fall within the continuous power dissipation ratings.

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T <sub>A</sub> = 25°C	T <sub>A</sub> = 70°C POWER RATING		
D	725 mW	5.8 mW/°C	464 mW		
Р	1000 mW	8.0 mW/°C	640 mW		

### recommended operating conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V <sub>CC</sub>	4.5	5	5.5	V
High-level input voltage, VIH	2			V
Low-level input voltage, V <sub>IL</sub>			0.8	V
Operating free-air temperature, T <sub>A</sub>	0		70	°C

# SN75476 THRU SN75478 DUAL PERIPHERAL DRIVERS

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## electrical characteristics over recommended operating free-air temperature range

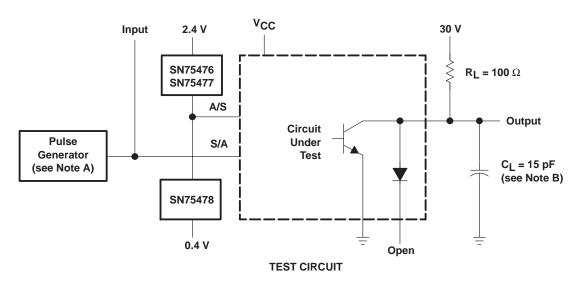
PARAMETER		TEST CONDITIONS		MIN	TYP <sup>†</sup>	MAX	UNIT	
VIK	Input clamp voltage		I <sub>I</sub> = -12 mA	I <sub>I</sub> = -12 mA		-0.95	-1.5	V
			V <sub>CC</sub> = 4.5 V,	I <sub>OL</sub> = 100 mA		0.16	0.3	
VOL	Low-level output voltage		$V_{IH} = 2 V$	$I_{OL} = 175 \text{ mA}$		0.22	0.5	V
			V <sub>IL</sub> = 0.8 V	$I_{OL} = 300 \text{ mA}$		0.33	0.6	
V <sub>O</sub> (BR)	Output breakdown voltage		$V_{CC} = 4.5 \text{ V},$	I <sub>OH</sub> = 100 μA	70	100		V
V <sub>R(K)</sub>	Output clamp reverse voltage		$V_{CC} = 4.5 \text{ V},$	I <sub>R</sub> = 100 μA	70	100		V
V <sub>F(K)</sub>	Output clamp forward voltage		$V_{CC} = 4.5 \text{ V},$	$I_F = 300 \text{ mA}$	0.8	1.15	1.6	V
ЮН	High-level output current		V <sub>CC</sub> = 4.5 V, V <sub>IL</sub> = 0.8 V,	V <sub>IH</sub> = 2 V, V <sub>OH</sub> = 70 V		1	100	μΑ
Iн	High-level input current		V <sub>CC</sub> = 5.5 V,	V <sub>I</sub> = 5.5 V		0.01	10	μΑ
1	Low lovel input ourrent	A input	V 55V	V <sub>I</sub> = 0.8 V		-80	-110	μА
¹IL	Low-level input current	S input	V <sub>CC</sub> = 5.5 V,			-160	-220	
	Supply current, outputs high	SN75476		V <sub>I</sub> = 5 V		10	17	
ІССН		SN75477	V <sub>CC</sub> = 5.5 V	V <sub>I</sub> = 0		10	17	mA
		SN75478	7	V <sub>I</sub> = 5 V		10	17	
	Supply current, outputs low	SN75476		V <sub>I</sub> = 0		54	75	
ICCL		SN75477	V <sub>CC</sub> = 5.5 V	V <sub>I</sub> = 5 V		54	75	mA
		SN75478		V <sub>I</sub> = 0		54	75	

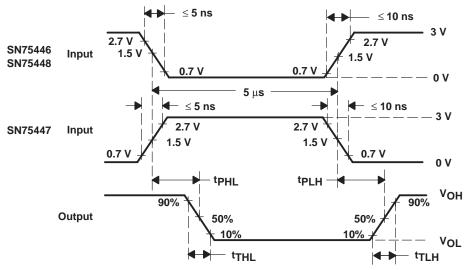
<sup>†</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

# switching characteristics, $V_{CC}$ = 5 V, $T_A$ = 25°C

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low-to-high-level output				200	350	ns
tPHL	Propagation delay time, high-to-low-level output	C <sub>L</sub> = 15 pF,	$R_L = 100 \Omega$ ,		200	350	ns
<sup>†</sup> TLH	Transition time, low-to-high-level output	See Figure 1			50	125	ns
<sup>t</sup> THL	Transition time, high-to-low-level output				90	125	ns
Vон	High-level output voltage after switching	V <sub>S</sub> = 55 V, See Figure 2	$I_O \approx 300 \text{ mA},$	V <sub>S</sub> -18			mV

### PARAMETER MEASUREMENT INFORMATION





**VOLTAGE WAVEFORMS** 

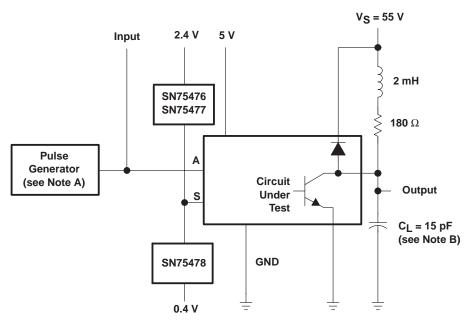
NOTES: A. The pulse generator has the following characteristics: PRR = 100 kHz,  $Z_O$  = 50  $\Omega$ .

B. C<sub>L</sub> includes probe and jig capacitance.

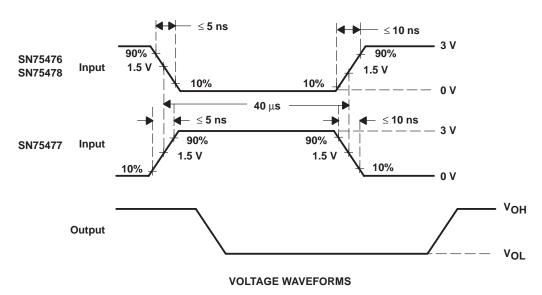
Figure 1. Test Circuit and Voltage Waveforms, Switching Characteristics



### PARAMETER MEASUREMENT INFORMATION



**TEST CIRCUIT** 



NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz,  $Z_O$  = 50  $\Omega$ .

B. C<sub>L</sub> includes probe and jig capacitance.

Figure 2. Latch-Up Test Circuit and Voltage Waveforms



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